



Standard Rectifier Module

$$V_{RRM} = 2 \times 1200 \text{ V}$$

$$I_{FAV} = 71 \text{ A}$$

$$V_F = 1.14 \text{ V}$$

Phase leg

Part number

MDD56-12N1B



Backside: isolated



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

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Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage				1300	V	
V_{RRM}	max. repetitive reverse blocking voltage				1200	V	
I_R	reverse current	$V_R = 1200\text{ V}$			200	μA	
		$V_R = 1200\text{ V}$			10	mA	
V_F	forward voltage drop	$I_F = 100\text{ A}$			1.21	V	
		$I_F = 200\text{ A}$			1.48	V	
		$I_F = 100\text{ A}$			1.14	V	
		$I_F = 200\text{ A}$			1.45	V	
I_{FAV}	average forward current	$T_C = 100^\circ\text{C}$			71	A	
$I_{F(RMS)}$	RMS forward current	180° sine			150	A	
V_{F0}	threshold voltage	} for power loss calculation only			0.80	V	
r_F	slope resistance				3	m Ω	
R_{thJC}	thermal resistance junction to case				0.51	K/W	
R_{thCH}	thermal resistance case to heatsink			0.2		K/W	
P_{tot}	total power dissipation				245	W	
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine			1.40	kA	
		t = 8,3 ms; (60 Hz), sine			1.51	kA	
		t = 10 ms; (50 Hz), sine			1.19	kA	
		t = 8,3 ms; (60 Hz), sine			1.29	kA	
I^2t	value for fusing	t = 10 ms; (50 Hz), sine			9.80	kA ² s	
		t = 8,3 ms; (60 Hz), sine			9.49	kA ² s	
		t = 10 ms; (50 Hz), sine			7.08	kA ² s	
		t = 8,3 ms; (60 Hz), sine			6.87	kA ² s	
C_J	junction capacitance	$V_R = 400\text{ V}; f = 1\text{ MHz}$		27		pF	



Package TO-240AA				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I_{RMS}	RMS current	per terminal			200	A	
T_{VJ}	virtual junction temperature		-40		150	°C	
T_{op}	operation temperature		-40		125	°C	
T_{stg}	storage temperature		-40		125	°C	
Weight					76	g	
M_D	mounting torque		2.5		4	Nm	
M_T	terminal torque		2.5		4	Nm	
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	13.0	9.7		mm	
$d_{Spb/Apb}$		terminal to backside	16.0	16.0		mm	
V_{ISOL}	isolation voltage	t = 1 second			3600	V	
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA		3000	V	



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD56-12N1B	MDD56-12N1B	Box	36	458066

Similar Part	Package	Voltage class
MDD56-08N1B	TO-240AA	800
MDD56-14N1B	TO-240AA	1400
MDD56-16N1B	TO-240AA	1600
MDD56-18N1B	TO-240AA	1800

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$



Rectifier

$V_{0\ max}$	threshold voltage	0.8	V
$R_{0\ max}$	slope resistance *	1.8	mΩ



Outlines TO-240AA



General tolerance: DIN ISO 2768 class „c“





Rectifier

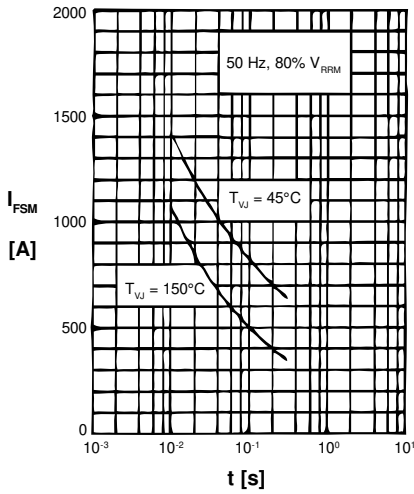


Fig. 1 Surge overload current
 I_{TSM}, I_{FSM} : Crest value, t : duration

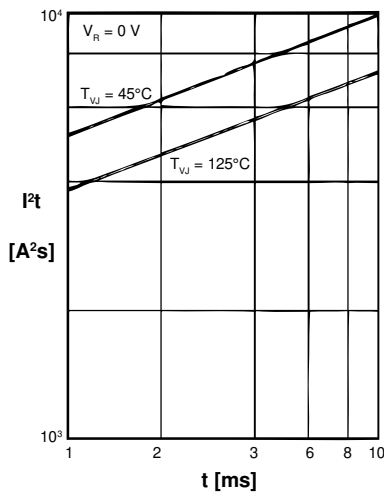


Fig. 2 I^2t versus time (1-10 ms)

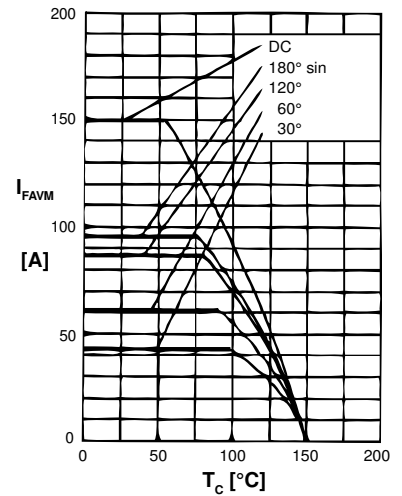


Fig. 3 Maximum forward current at case temperature

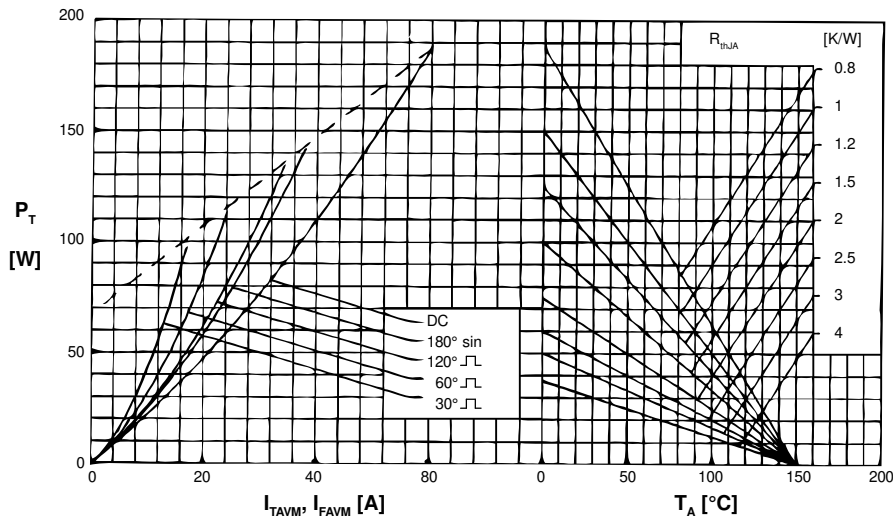


Fig. 4 Power dissipation vs. onstate current and ambient temperature (per diode)

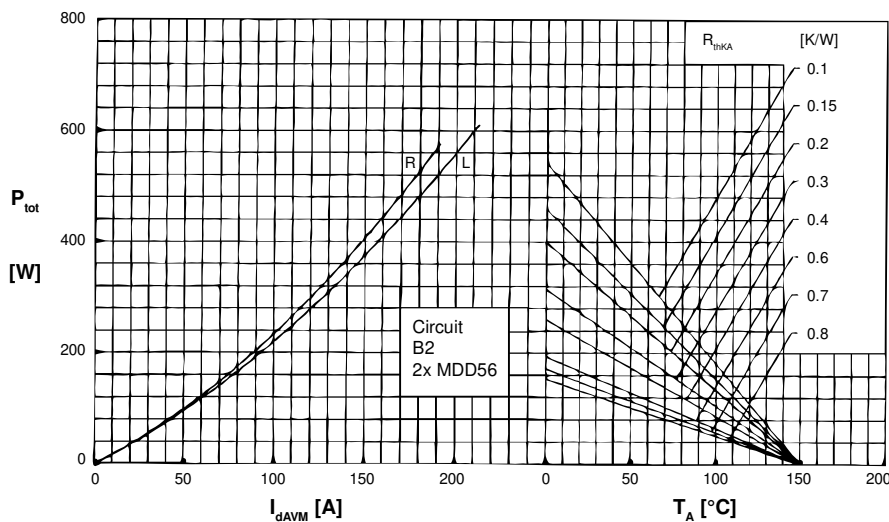


Fig. 6 Single phase rectifier bridge: Power dissipation versus direct output current and ambient temperature; R = resistive load, L = inductive load



Rectifier

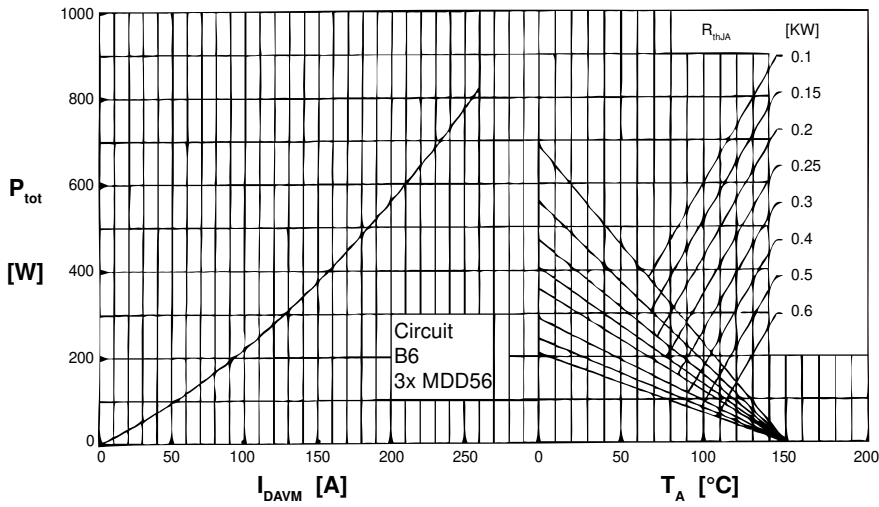


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

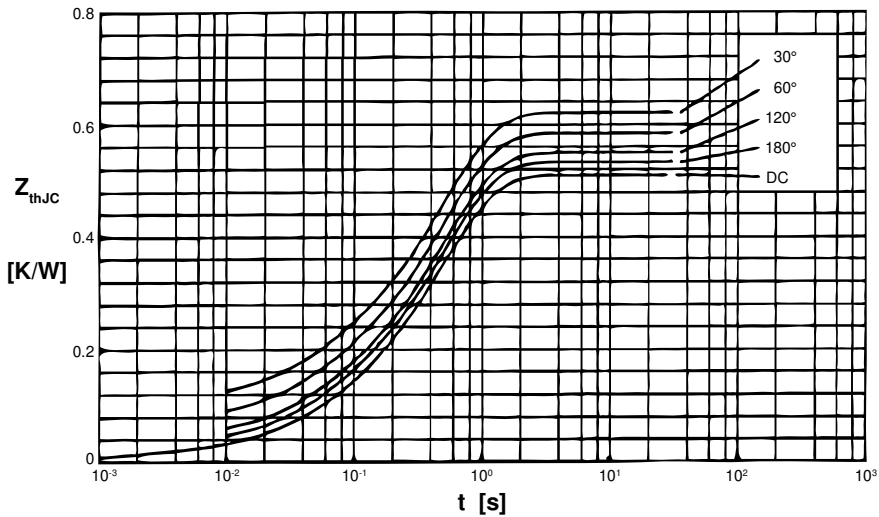


Fig. 7 Transient thermal impedance junction to case (per diode)

R_{thJC} for various conduction angles d:

d	R_{thJC} [K/W]
DC	0.51
180°	0.53
120°	0.55
60°	0.58
30°	0.62

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.013	0.0015
2	0.055	0.0450
3	0.442	0.4850

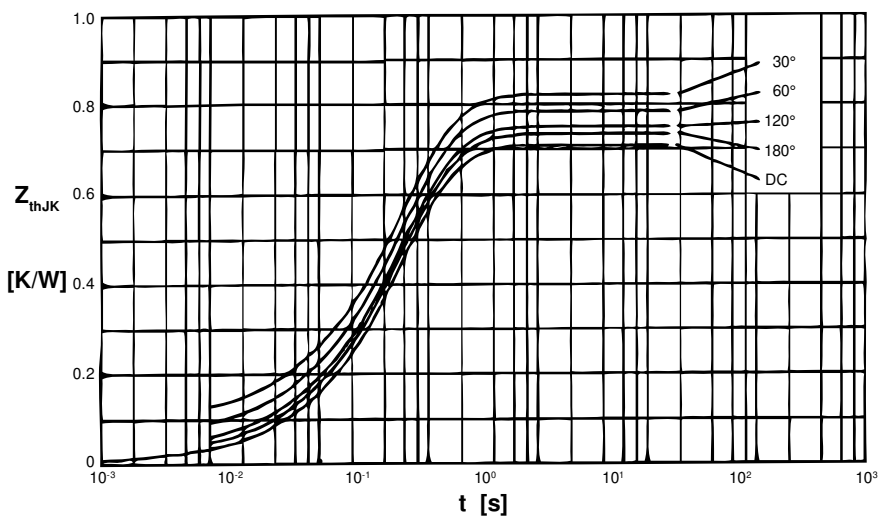


Fig. 8 Transient thermal impedance junction to heatsink (per thyristor)

R_{thJK} for various conduction angles d:

d	R_{thJK} [K/W]
DC	0.71
180°	0.73
120°	0.75
60°	0.78
30°	0.82

Constants for Z_{thJK} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.013	0.0015
2	0.055	0.0450
3	0.442	0.4850
4	0.200	1.2500